# **MOSFET** - Dual, N-Channel, **Small Signal**

# 20 V, 540 mA

#### **Features**

- Low R<sub>DS(on)</sub> Improving System Efficiency
- Low Threshold Voltage
- Small Footprint 1.6 x 1.6 mm
- ESD Protected Gate
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

## **Applications**

- Load/Power Switches
- Power Supply Converter Circuits
- Battery Management
- Cell Phones, Digital Cameras, PDAs, Pagers, etc.

#### **MAXIMUM RATINGS** (T<sub>.1</sub> = 25°C unless otherwise noted.)

Paramet	Symbol	Value	Unit		
Drain-to-Source Voltage	V <sub>DSS</sub>	20	V		
Gate-to-Source Voltage			$V_{GS}$	±7.0	V
Continuous Drain Current	Steady	Steady T <sub>A</sub> = 25°C		540	mA
(Note 1)	State	$T_A = 85^{\circ}C$	I <sub>D</sub>	390	
Power Dissipation (Note 1)	Stea	dy State	P <sub>D</sub>	250	mW
Continuous Drain Current (Note 1)	t ≤ 5 s	$T_A = 25^{\circ}C$	I <sub>D</sub>	570	mA
(Note 1)	1 3 0 3	$T_A = 85^{\circ}C$	טי	410	
Power Dissipation (Note 1)	t:	≤ 5 s	P <sub>D</sub>	280	mW
Pulsed Drain Current	I <sub>DM</sub>	1.5	Α		
Operating Junction and Sto	T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	ô		
Source Current (Body Diode	IS	350	mA		
Lead Temperature for Solde (1/8" from case for 10 s)	$T_L$	260	Ĉ		

#### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient - Steady State (Note 1)	$R_{ heta JA}$	500	°C/W
Junction-to-Ambient – $t \le 5$ s (Note 1)		447	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

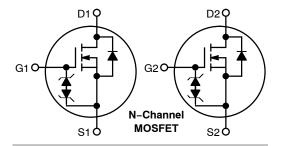
1. Surface mounted on FR4 board using 1 in sq pad size (Cu. area = 1.127 in sq [1 oz] including traces).



# ON Semiconductor®

#### www.onsemi.com

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub> Typ	I <sub>D</sub> Max (Note 1)		
	400 mΩ @ 4.5 V			
20	500 mΩ @ 2.5 V	540 mA		
	700 mΩ @ 1.8 V			



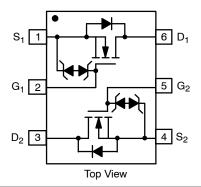


TV = Specific Device Code

= Date Code Μ = Pb-Free Package

(Note: Microdot may be in either location)

#### PINOUT: SOT-563



#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

## **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> = 25°C unless otherwise noted.)

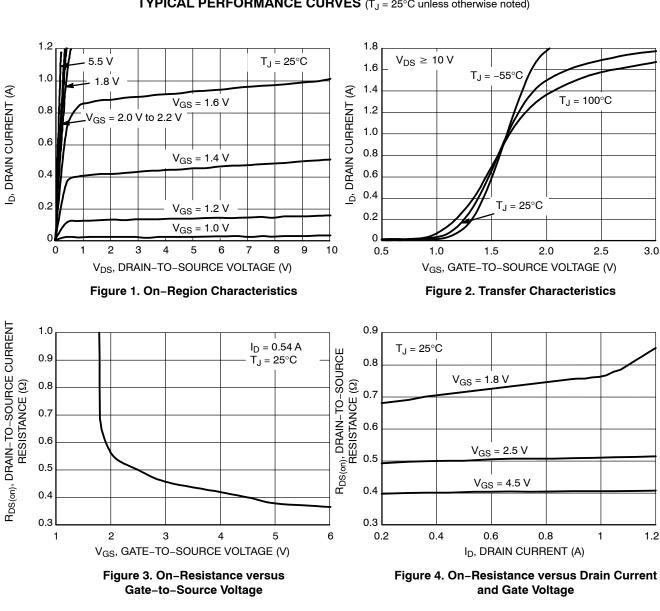
Parameter	Symbol	Test Condition		Min	Тур	Max	Unit	
OFF CHARACTERISTICS	•							
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		20	_	_	V	
Drain-to-Source Breakdown Voltage Temperature Coefficient	V <sub>(BR)DSS</sub> /T <sub>J</sub>	-	<del>-</del>		14	-	mV/°C	
Zero Gate Voltage Drain Current	ent V <sub>GS</sub> = 0 V		T <sub>J</sub> = 25°C	-	_	1.0	μΑ	
	I <sub>DSS</sub>	V <sub>DS</sub> = 16 V	T <sub>J</sub> = 125°C	-	_	5.0	1	
Gate-to-Source Leakage Current	I <sub>GSS</sub>	$V_{DS}$ = 0 V, $V_{GS}$ = ±	4.5 V	-	-	±5.0	μΑ	
ON CHARACTERISTICS (Note 3)								
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 25	0 μΑ	0.45	_	1.0	V	
Negative Threshold Temperature Coefficient	V <sub>GS(TH)</sub> /T <sub>J</sub>	-		-	2.0	-	mV/°C	
Drain-to-Source On Resistance		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 54	0 mA	-	0.4	0.55	Ω	
	R <sub>DS(on)</sub>	V <sub>GS</sub> = 2.5 V, I <sub>D</sub> = 50	0 mA	-	0.5	0.7		
		V <sub>GS</sub> = 1.8 V, I <sub>D</sub> = 350 mA			0.7	0.9		
Forward Transconductance	9FS	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 540 mA			1.0	_	S	
CHARGES AND CAPACITANCES	•			•	•			
Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> = 0 V, f = 1.0 MHz, V <sub>DS</sub> = 16 V		-	80	150	pF	
Output Capacitance	C <sub>OSS</sub>			-	13	25	1	
Reverse Transfer Capacitance	C <sub>RSS</sub>			-	10	20		
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 10 V; I <sub>D</sub> = 540 mA		-	1.5	2.5	nC	
Threshold Gate Charge	Q <sub>G(TH)</sub>			-	0.1	-		
Gate-to-Source Charge	Q <sub>GS</sub>			-	0.2	-	1	
Gate-to-Drain Charge	$Q_{GD}$			-	0.35	-		
SWITCHING CHARACTERISTICS, $V_{GS} = V$	Note 4)							
Turn-On Delay Time	t <sub>d(ON)</sub>			-	6.0	-	ns	
Rise Time	t <sub>r</sub>	$V_{GS}$ = 4.5 V, $V_{DD}$ = 10 V, $I_{D}$ = 540 mA, $R_{G}$ = 10 $\Omega$		-	4.0	-		
Turn-Off Delay Time	t <sub>d(OFF)</sub>			-	16	-		
Fall Time	t <sub>f</sub>	<u> </u>			8.0	-		
DRAIN-SOURCE DIODE CHARACTERISTIC	cs							
Forward Diode Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0 V,	T <sub>J</sub> = 25°C	-	0.7	1.2	V	
		I <sub>S</sub> = 350 mA	T <sub>J</sub> = 125°C	-	0.6	-		
Reverse Recovery Time	t <sub>RR</sub>	$V_{GS} = 0 \text{ V}, d_{ISD}/d_t = 100 \text{ A}/\mu \text{s}$	s, I <sub>S</sub> = 350 mA	-	6.5	_	ns	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Surface–mounted on FR4 board using 1 in. sq. pad size (Cu. area = 1.127 in sq [1 oz] including traces).

- Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
   Switching characteristics are independent of operating junction temperatures.

## TYPICAL PERFORMANCE CURVES (T<sub>J</sub> = 25°C unless otherwise noted)



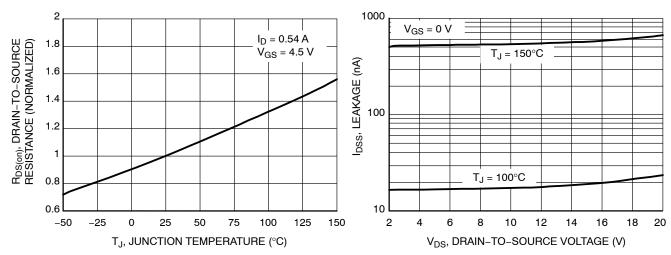
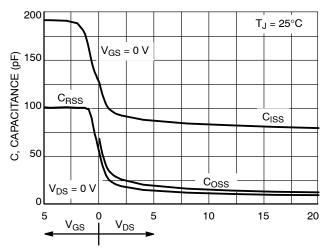


Figure 5. On-Resistance Variation with **Temperature** 

Figure 6. Drain-to-Source Leakage Current versus Voltage

# TYPICAL PERFORMANCE CURVES (T<sub>J</sub> = 25°C unless otherwise noted)



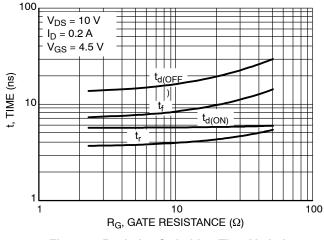
 $^{\circ}$   $^{\circ}$   $^{\circ}$   $^{\circ}$   $^{\circ}$   $^{\circ}$   $^{\circ}$   $^{\circ}$   $^{\circ}$   $^{\circ}$  OPAIN–TO–SOURCE VOLTAGE (V) V<sub>GS</sub>, GATE-TO-SOURCE VOLTAGE (V)  $V_{DS}$  $V_{GS}$  $Q_{GS}$  $Q_{GD}$  $I_D = 0.54 A$  $T_J = 25^{\circ}C$ 0 0.2 0 0.4 0.6 0.8 1.2 1.4 1.6 Qg, TOTAL GATE CHARGE (nC)

 $\mathsf{Q}_\mathsf{T}$ 

GATE-TO-SOURCE OR DRAIN-TO-SOURCE VOLTAGE (V)

Figure 8. Gate-to-Source and **Drain-to-Source Voltage versus Total Charge** 





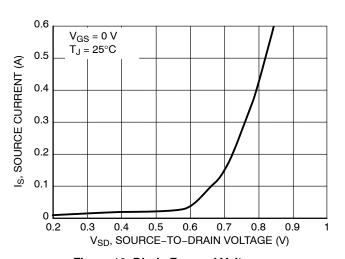


Figure 9. Resistive Switching Time Variation versus Gate Resistance

Figure 10. Diode Forward Voltage versus Current

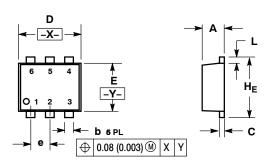
#### **ORDERING INFORMATION**

Device	Package	Shipping		
NTZD3154NT1G				
NTZD3154NT1H		4000 / Taga & Basil		
NTZD3154NT2G	SOT-563	4000 / Tape & Reel		
NTZD3154NT2H	(Pb-Free)			
NTZD3154NT5G		0000 / Tana & Daal		
NTZD3154NT5H		8000 / Tape & Reel		

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### PACKAGE DIMENSIONS

#### SOT-563, 6 LEAD CASE 463A **ISSUE F**

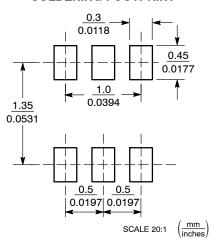


#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI
- JUNEAU DINING AND FOLL FARMING FELL MANN
  714.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETERS
  MAXIMUM LEAD THICKNESS INCLUDES LEAD
  FINISH THICKNESS. MINIMUM LEAD THICKNESS
  IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MIL	LIMETE	RS	INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.50	0.55	0.60	0.020	0.021	0.023	
b	0.17	0.22	0.27	0.007	0.009	0.011	
С	0.08	0.12	0.18	0.003	0.005	0.007	
D	1.50	1.60	1.70	0.059	0.062	0.066	
Е	1.10	1.20	1.30	0.043	0.047	0.051	
е	0.5 BSC			0.02 BSC			
L	0.10	0.20	0.30	0.004	0.008	0.012	
He	1.50	1.60	1.70	0.059	0.062	0.066	

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and (III) are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any reserves the right to make dranges without further holice to any products herein. Scilled makes no warrany, representation or guarantee regarding the suitability of its products of which particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its pattent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all Claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## **PUBLICATION ORDERING INFORMATION**

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910 Japan Customer Focus Center

Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative